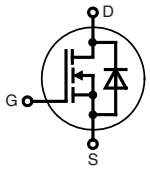
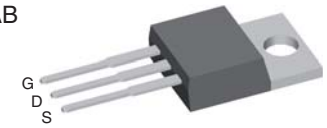
CoolMOS™ [1] Power MOSFET

N-Channel Enhancement Mode
Low R_{DSon}, High V_{DSS} MOSFET
Ultra low gate charge

I_{D25} = 13 A
V_{DSS} = 600 V
$R_{DS(on)\ max}$ = 0.3 Ω



TO-220 AB



MOSFET			
Symbol	**Conditions**	**Maximum Ratings**	
V_{DSS}	T_{VJ} = 25°C	600	V
V_{GS}		± 20	V
I_{D25}	T_C = 25°C	13	A
I_{D90}	T_C = 90°C	9	A
E_{AS}	single pulse } I_D = 4.4 A; T_C = 25°C	290	mJ
E_{AR}	repetitive } I_D = 4.4 A; T_C = 25°C	0.44	mJ
dV/dt	MOSFET dV/dt ruggedness V_{DS} = 0...480 V	50	V/ns

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
R_{DSon}	V_{GS} = 10 V; I_D = 6.6 A		270	300	mΩ
$V_{GS(th)}$	V_{DS} = V_{GS}; I_D = 0.44 mA	2.5	3	3.5	V
I_{DSS}	V_{DS} = 600 V; V_{GS} = 0 V; T_{VJ} = 25°C			1	µA
	V_{DS} = 600 V; V_{GS} = 0 V; T_{VJ} = 125°C		10		µA
I_{GSS}	V_{GS} = ± 20 V; V_{DS} = 0 V			100	nA
C_{iss}	V_{GS} = 0 V; V_{DS} = 100 V, f = 1 MHz		1100		pF
C_{oss}	V_{GS} = 0 V; V_{DS} = 100 V, f = 1 MHz		60		pF
Q_g	V_{GS} = 0 to 10 V; V_{DS} = 400 V; I_D = 6.6 A		20	30	nC
Q_{gs}	V_{GS} = 0 to 10 V; V_{DS} = 400 V; I_D = 6.6 A		5		nC
Q_{gd}	V_{GS} = 0 to 10 V; V_{DS} = 400 V; I_D = 6.6 A		7.6		nC
$t_{d(on)}$	V_{GS} = 10 V; V_{DS} = 400 V; I_D = 6.6 A; R_G = 4.3 Ω		10		ns
t_r	V_{GS} = 10 V; V_{DS} = 400 V; I_D = 6.6 A; R_G = 4.3 Ω		5		ns
$t_{d(off)}$	V_{GS} = 10 V; V_{DS} = 400 V; I_D = 6.6 A; R_G = 4.3 Ω		40		ns
t_f	V_{GS} = 10 V; V_{DS} = 400 V; I_D = 6.6 A; R_G = 4.3 Ω		5		ns
R_{thJC}				0.95	K/W

Features

- fast CoolMOS™ [1] power MOSFET 4th generation
  - High blocking capability
  - Lowest resistance
  - Avalanche rated for unclamped inductive switching (UIS)
  - Low thermal resistance due to reduced chip thickness
- Enhanced total power density

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

[1] CoolMOS™ is a trademark of Infineon Technologies AG.

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Source-Drain Diode

Symbol	Conditions	Characteristic Values (T_{VJ} = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V			6.6	A
V_{SD}	I_F = 6.6 A; V_{GS} = 0 V		0.9	1.2	V
t_{rr}	I_F = 6.6 A; $-di_F/dt$ = 100 A/µs; V_R = 400 V		300		ns
Q_{RM}			3.9		µC
I_{RM}			26		A

Component

Symbol	Conditions		Maximum Ratings	
T_{VJ}	operating		-55...+150	°C
T_{stg}			-55...+150	°C
M_d	mounting torque	TO-247	0.8 ... 1.2	Nm
		TO-220	0.4 ... 0.6	Nm

Symbol	Conditions		Characteristic Values min.	typ.	max.	
R_{thCH}	with heatsink compound	TO-247		0.25		K/W
		TO-220		0.50		K/W
Weight	TO-247			6		g
	TO-220			2		g

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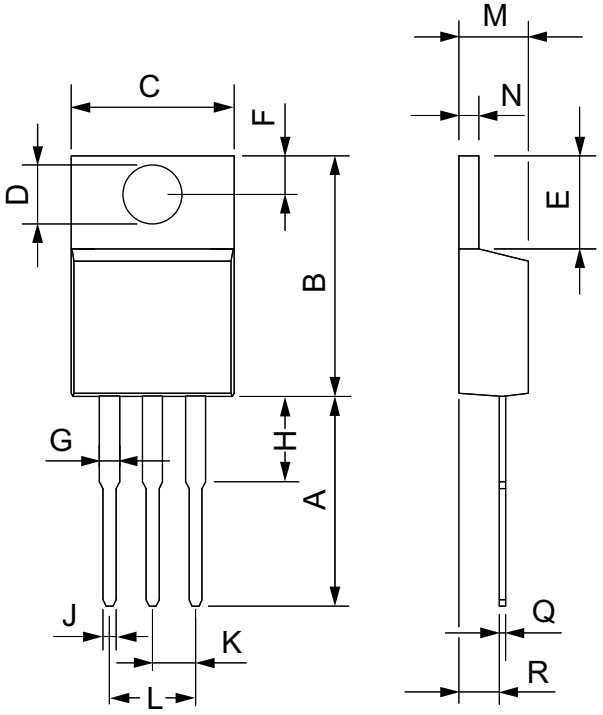
TO-220 AB Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

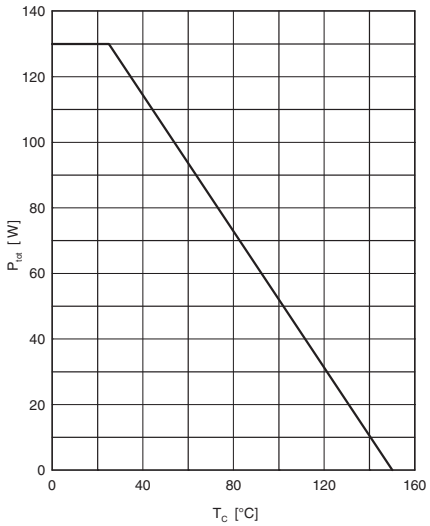


Fig. 1 Power dissipation

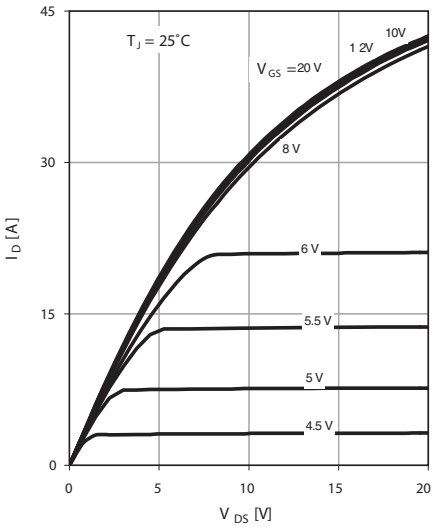


Fig. 2 Typ. output characteristics

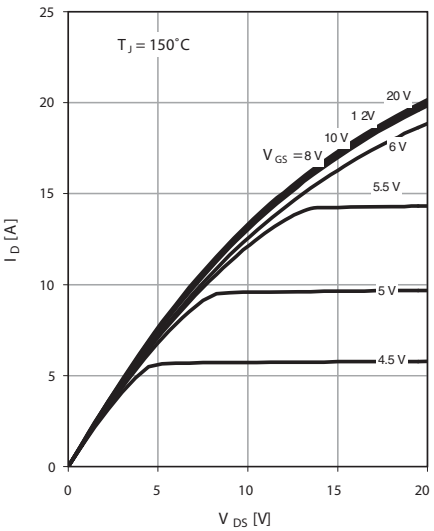


Fig. 3 Typ. output characteristics

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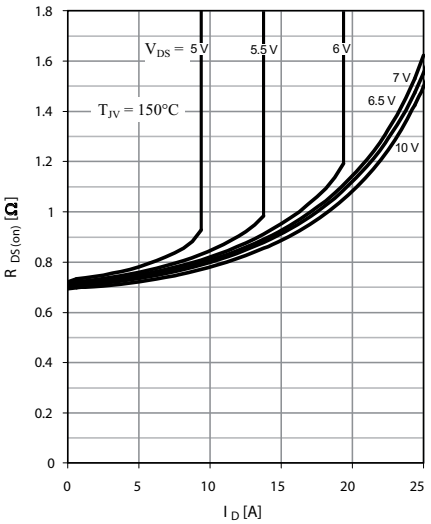

Fig. 4 Typ. drain-source on-state resistance characteristics of IGBT

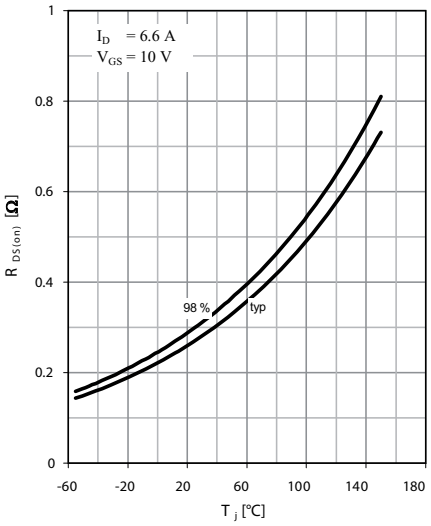

Fig. 5 Drain-source on-state resistance

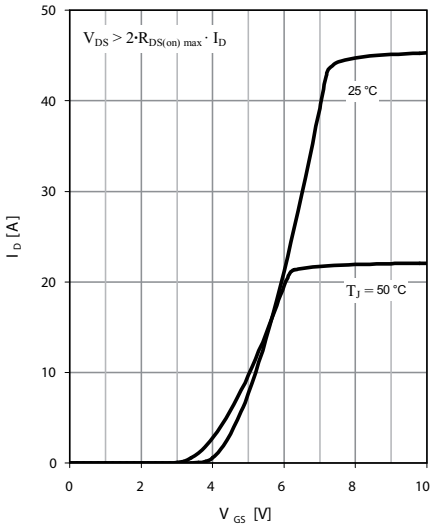

Fig. 6 Typ. transfer characteristics

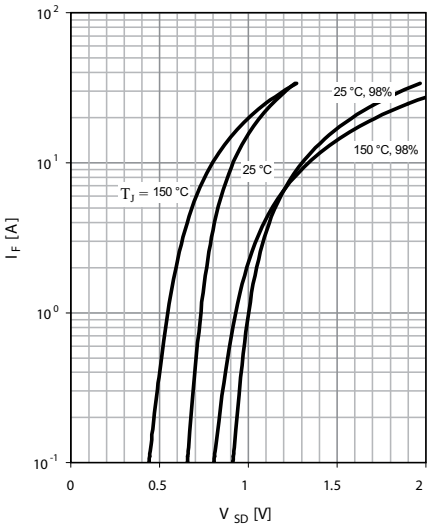

Fig. 7 Forward characteristic of reverse diode

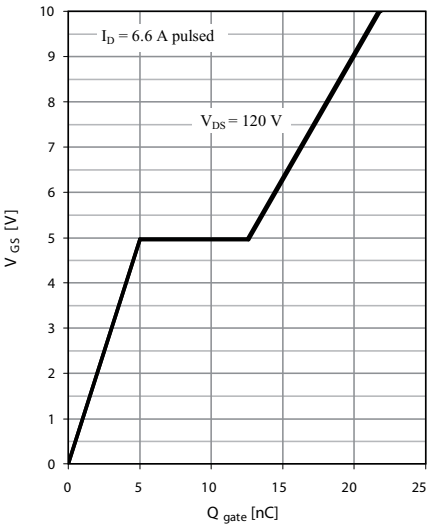

Fig. 8 Typ. gate charge

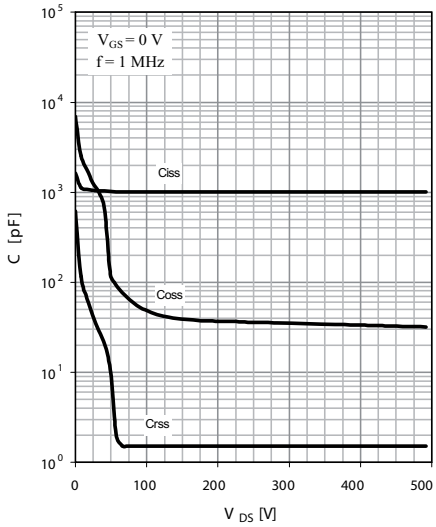

Fig. 9 Typ. capacitances

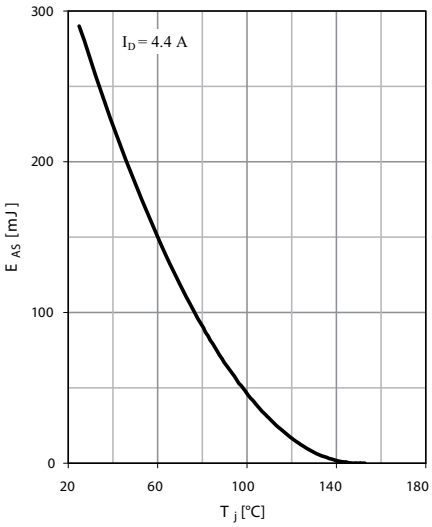

Fig. 10 Avalanche energy

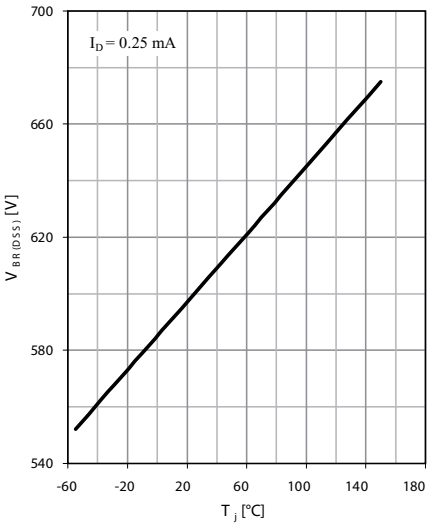

Fig. 11 Drain-source breakdown voltage

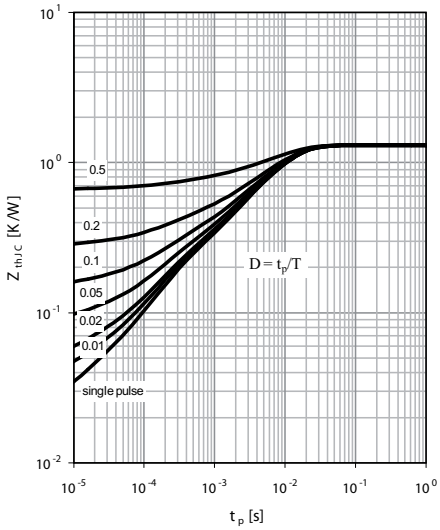

Fig. 12 Max. transient thermal impedance

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